Amendments to the Claims:

The following listing replaces all prior listing of claims in the application.

Listing of Claims:

1. (Currently amended) A method of fabricating a stacked structure comprising the following sequential steps:

a) selecting a first plate and a second plate such that a surface portion of ~~at least one of~~ the first plate ~~and second plates has a surface having~~ has a roughness such that the surface portion is incapable of sticking to a surface of ~~another~~ the second plate,

b) producing a sacrificial layer on at least a part of the surface of the first plate or the surface of the second plate, and

c) bonding the first and second plates together,

the method further comprising a step of at least partly eliminating the sacrificial layer to expose the surface portion such that the surface portion at least partially faces the ~~other~~ second plate.

2. – 4. (Cancelled)

5. (Previously presented) The method according to claim 1 wherein selecting a first plate and a second plate further comprises forming the surface having a roughness by increasing the roughness of the selected first or second plate to greater than approximately 0.2 nm root-mean-square (RMS).

6. (Previously presented) The method according to claim 1 wherein selecting comprises selecting a least one of the plates that initially includes a surface layer.

7. (Previously presented) The method according to claim 6, wherein selecting further comprises selecting at least one of the plates wherein the surface layer comprises a monocrystalline surface layer.

8. (Previously presented) The method according to claim 6 wherein selecting further comprises selecting at least one of the plates wherein the surface layer comprises silicon.

9. – 10. (Cancelled)

11. (Previously presented) The method according to claim 1 further comprising forming a surface layer comprising silicon nitride on one of the first or second plates.

12. (Previously presented) The method according to claim 1 further comprising smoothing at least one of a free surface of the sacrificial layer or a free surface of at least one of the plates before the bonding.

13. (Previously presented) The method according to claim 1 further comprising smoothing the free surface of the sacrificial layer and the free surface of at least one of the plates before the bonding.

14. (Previously presented) The method according to claim 1 wherein bonding comprises molecular bonding.

15. (Previously presented) The method according to claim 1 wherein bonding comprises bonding with a sacrificial bonding agent.

16. (Previously presented) The method according to claim 1 wherein bonding further comprises bonding assisted by at least one of a mechanical means, a plasma treatment, or a thermal treatment.

17. (Previously presented) The method according to claim 1 wherein the method further comprises applying a selected atmosphere before bonding.

18. (Previously presented) The method according to claim 16 wherein assisting further comprises applying a selected atmosphere during bonding.

19. (Previously presented) The method according to claim 16 wherein bonding further comprises exposing the two plates to an open air environment before bonding.

20. (Previously presented) The method according to claim 16 wherein bonding further comprises bonding in an open air environment.

21. (Previously presented) The method according to claim 1 further comprising thinning at least one of the first or second plates after bonding.

22. (Previously presented) The method according to claim 1 wherein a major portion of at least one of the plates comprises a semiconductor material.

23. (Previously presented) The method according to claim 22 wherein the major portion comprises silicon.

24. (Previously presented) The method according to claim 1 wherein the sacrificial layer comprises silicon oxide.

25. (Previously presented) The method according to claim 1 wherein the sacrificial layer comprises a polymer.

26. (Previously presented) A stacked structure fabricated by a method according to claim 1.

27. – 41. (Cancelled)